Curriculum and Syllabus for M.Tech.

Electronics and Communication Engineering With Specialization in Microelectronics and VLSI Systems

From The Academic Year 2021

(Approved by Senate-44)



Indian Institute of Information Technology, Design and Manufacturing, Kancheepuram

Chennai-600 127

		Semester 1					
S.No	Couse Code	Course Name	Category	L	Т	Р	С
1	EC5009	MOSFET Modelling for VLSI Circuits	PCC	3	1	0	4
2	EC5010	Analog IC Design	PCC	3	1	0	4
3	EC5011	VLSI Testing and Testable Design	PCC	3	1	0	4
4		Professional Elective Course 1	PEC	3	1	0	4
5		Professional Elective Course 2	PEC	3	1	0	4
6	EC5012	Device Modelling and Simulation Practice	PCC	0	0	3	1.5
7	EC5013	SoPC and VLSI Testing Practice	PCC	0	0	3	1.5
							23.0
		Semester 2		•			•
S.No	Course Code	Course Name	Category	L	Т	Р	С
1	EC5014	Digital IC Design	PCC	3	1	0	4
2	EC5015	VLSI System Design	PCC	3	1	0	4
3	EC5016	VLSI Technology	PCC	3	1	0	4
4		Professional Elective Course 3	PEC	3	1	0	4
5		Professional Elective Course 4	PEC	3	1	0	4
6	EC5017	IC Design Practice#	PCC	0	0	4	2
7	EC5018	High level verification with System Verilog and UVM\$	PCC	2	0	4	4
\$ - As	per Senate 50,	he credit type was changed from 0 0 3 1.5 to 0 0 4 the course name was changed to High level ver (M (2 0 4 4) from Verification Practice (0 0 3 1.5).					26.0
		Semester 3		1			
S.No	Course Code	Course Name	Category	L	Т	Р	С
1	EC6003	MT-EC-MVS-Project Phase I (May-July)(Summer Internship)	PCD	0	0	20	10
2	EC6004	MT-EC-MVS-Project Phase II (Aug-Nov)	PCD	0	0	32	16
	1						26.0
		Semester 4		1	1		1
S.No	Course Code	Course Name	Category	L	Т	Р	С
1	EC6005	MT-EC-MVS-Project Phase III (Dec-Apr)	PCD	0	0	32	16
							16.0

- 1. Professional Elective Course is an elective course offered or prescribed by the parent department.
- 2. In line with the guidelines approved by the Senate (Senate 46-07), an M.Tech student can earn a maximum of 6 credits from NPTEL Courses. For all successfully completed NPTEL Courses, the letter grade "H" (Pass) will be awarded and credits of such courses will not be accounted for CGPA calculation.

Semester wise Credit Distribution

Semester								
Category	S1	S2	S3	S4	Total	%		
Professional Core Course (PCC)	15	18	0	0	33	34.1		
Professional Elective Course (PEC)	8	8	0	0	16	18.2		
Professional Career Development (PCD)	0	0	26	16	42	47.7		
Total	23.0	26.0	26.0	16.0	91.0	100.0		
	23.0	49.0	75.0	91.0				

Course Name	MOSFET Modelling for VLSI Circuits	Course Code	EC5009	EC5009				
Offered by Department	Electronics and Communication Engineering	Structure(LTPC)	3	1	0	4		
To be offered for	M.Tech	Course Type	Core			•		
Prerequisite	Basics of Semiconductor Devices, Digital Electronics	Approved In	Senate	-44				
Learning Objectives	 To demonstrate and apply basic concepts of semiconductor physics relevant to devices To describe and use physics-based numerical and analytical device modelling for the inclusion in circuit applications 							
Learning Outcomes	At the end of the course, the students would be able to • Model any kind of MOS Devices in 2-D or 3-D • Relate the models for further inclusion in circuits							
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	Voltage, Surface Condition, Inversion, Small- Signal Cap Long-Channel MOS Transis Models, Weak Inversion Models, Charge Sharing, Drain-Inductors of Charge Sharing, and Properties Parameter Extraction, Comp. Small-Signal Modelling - Circuits, Conductance Parameter Extraction, Source Definitions and Equivalent Parameter Model, RF Model	 Intuitive analysis of MOS Transistor- Two-Terminal MOS Structure – Flatband Voltage, Surface Condition, General Analysis, Inversion, Strong Inversion, Weak Inversion, Small- Signal Capacitance, Three-Terminal MOS Structure (7L+3T) Long-Channel MOS Transistor, Introduction All-Region Models, Strong Inversion Models, Weak Inversion Models, Source Reference vs. Body Reference, Effective Mobility (5L+2T) Small-Dimension Effects - Velocity Saturation, Channel Length Modulation, Charge Sharing, Drain-Induced Barrier Lowering, Hot Carrier Effects, Velocity Overshoot Ballistic Operation, Polysilicon Depletion (6L+2L) Small-Dimension Effects-Modelling for Circuits Simulation- Quantum-Mechanical Effects; Gate Current, Junction Leakage, Scaling and New Technologies, Approaches, and Properties of Good Models, Model Formulation Considerations, Parameter Extraction, Compact Models, Benchmark Tests (7L+3L) Small-Signal Modelling - Conductance Parameter Definitions and Equivalent Circuits, Conductance Parameters Due to Gate and Body Leakage, 						
Essential Reading	1. Y. Tsividis and C. McAndrew, Mc University Press, 2011			t Simula	tion, Ox	ford		
Supplementary Reading	 BSIM Manuals available on BSIM T. A. Fjeldly, T. Yetterdal and M. Simulation, John Wiley, 1998. Y. Taur and T. H. Ning, Fundam Press, 1998. Y. P. Tsividis, Mixed Analog-digit Publishing Co Pte Ltd, 2002 	M. Shur, Introduct	ion to De	ices, Car	nbridge	University		

Course Name	Analog IC Design	Course Code	EC5010)			
Offered by	Electronics and Communication	Structure	3	1	0	4	
Department	Engineering	(LTPC)	0	1	U	4	
To be offered for	M.Tech	Course Type	Core				
Prerequisite	NIL	Approved In	Senate-	-44			
Learning Objectives	design and analysis of operat	art in depth knowledge in CMOS based analog circuits, performance metrics, and analysis of operational amplifiers and circuits using them apable of designing an opamp for given specifications					
Learning Outcomes	 To analyses effect of mismatch between components in the performance of ICs To model MOSFET in IC To analyses noise in different components in the IC To derive the Data Sheet / Specifications of Single stage, two stage, folded cascade opamps To understand fully differential operation, opamp and make such circuits 						
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	 Components and mismatch in CMOS process, models and Layout techniques. (4L+2T) MOS Transistor: Layout, model, Body effect, transit frequency. (4L+2T) Noise: Noise in Resistor, capacitor, and MOSFET, spectral density (4L+2T) Single stage opamp: Noise, offset, swing limits and slew rate, Loop gain and stability Analysis in two and higher order opamp (10L+2T) Cascode current mirror, Cascode, Folded Cascode multi stage and Miller compensated op amps. (8L+2T) Fully differential circuits and opamp, common mode feedback circuits. (6L+2T) PLL (6L+2T) Tutorials will include pen-paper analysis and circuit simulation at schematic and layout level 						
Essential Reading	1. Behzad Razavi, Design of Analog Education, 2016, ISBN: 978-0-07	-252493-2					
Supplementary Reading	1. Tony Chan Carusone, David A. Johns, Kenneth W. Martin, Analog Integrated Circuit Design, John Wiley & Sons, Inc., 2012, ISBN: 978-0-470-77010-8. 2. Paul R. Gray, Paul J. Hurst, Stephen H. Lewis, Robert G. Meyer, Analysis and Design Of Analog Integrated Circuits 5th edition. John Wiley & Song Inc., 2000, ISBN: 978-0-100-1000.						

Course Name	VLSI Testing and Testable Design	Course Code	EC50	11					
Offered by	Electronics and Communication	Structure(LTP	3	1	0	4			
Department	Engineering	C)	3	1	U	4			
To be offered for	M.Tech	Course Type	Core						
Prerequisite	Basics of Digital Electronics	Approved In	Senat						
Learning Objectives	The course aims at imparting testable circuit and optimal testable.	-		_	of an e	fficient			
Learning Outcomes	 At the end of the course, the s Model the faults in the combin Perform the fault analysis and Build the testable circuit with 	 Model the faults in the combination and sequential circuits Perform the fault analysis and test pattern generation using ATPG algorithms Build the testable circuit with test vectors. 							
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	 Basic of Test and Role of Hild Digital System Test, ATE Archiverillog HDL for Design and Test, Basic Structures of Verifer Testbench Techniques. (3L+1T) Fault and Defect Modelling: Issues Related to Gate Level For Fault Simulation Application: Applications, Fault Simulation: Applications, Fault Simulation: Test pattern Generation Mecontrollability and Observabil Deterministic Test Generation Methods, Sequential Circuit Test Generation, Full Scan DFT Test Design (4L+2T) Standard IEEE Test Access In Architecture, Boundary Scan Structure, RT level Boundary (5L+2T) Logic Built-in Self-test: BIST In Analysis, BIST Architectures, Test Compression: Test Decompression Methods. (3L+1) Memory Testing by Means Structure. (2L+1T) 	Test: Using Verilouslog, Combinationally) Fault Modelling, Fault Modelling, Fault Modelling, Fault Collapsed Methods: Fault Technologies. (5L-thods and Algoritity, Random Test Gon Algorithms: Dest Generation, Test Generation, Test of Scan: Making Chnique, Scan Architecture, Scan and Boundary Scan and Boundary Scan and Boundary Test Instruction Scan and Boundary Rasics, Test Pattern RT Level BIST Destata Compression, 1T)	structure sing in Total structure sing in Total structure that a circuit shitecture y Scan and Generating sign. (4 Comp	ral Gate Verilog. ation, Fa est Gen ion, (4L+ nistic Te Compact s Testal res and Basics, rd Leve Descrip ration, O LL+1T) ression	(3L+1T) sing Verential Circle Level (5L+2T) ault Simpler (5L+2T) ault Simpler (5L) est Generation (4I) ble, Test RT level Boundary el Scantion Lanutput Re Method	prilog in ircuits, Faults, ulation Basics, eration +1T) tability cl Scan Chain guage. sponse s and			
Essential Reading	ZainalabedinNavabi, Test a Architecture, 1 st edition, Sprir		_	_		ls and			
Supplementary Reading	 M. Abramovici, M. A. Breuer Testable Design, Wiley-IEEE Niraj K. Jha, Sandeep Gu Cambridge University Press, 2 Michael L. Bushnell, Vishwar Digital, Memory, and Mixed-S 7991-8. 	and A. D. Figriiet. Press, 1994, ISBN: pta, Testing of 2003. ISBN: 0521-7 ii D. Agrawal, Esse	a, Digit 978-0-7 Digital 7356-3 entials o	al Syste: 7803-106 System of Electro	ms Testi 2-9. s, 1st e	edition,			

Course Name	Device Modelling and Simulation Practice	Course Code	EC5012	2				
Offered by Department	Electronics and Communication Engineering	Structure(LTP C)	0	0	3	1.5		
To be offered for	M.Tech	Course Type	Core					
Prerequisite	NIL	Approved In	Senate					
Learning Objectives	 To make the students familiar with semiconductor device Physics. To impart a flavour of different semiconductor device modelling with the help of simulation tools. The lab is intended to teach students about device structure and provide confidence to design the device structure and plotting necessary characteristics in relevant device modelling tools. 							
Learning Outcomes	At the end of the course, students would be able to: • simulate and analyse structure, doping profile, terminal characteristics and distributions of carriers, current, field, potential and energy band diagrams within 2-dimensional device structures							
Course Contents (with approximate breakup of hours for lecture/tutorial/practice)	of device and process simulat Device simulation: observing carriers, current, field, potential Process simulation: observation Simulation of 2-D MOSFETs Simulation of novel 3-D training simulation of simulation	 Introduction to Technology computer aided design (TCAD) tools; inputs and outputs of device and process simulations. Device simulation: observing the terminal characteristics and distributions of carriers, current, field, potential and energy band diagrams within the device. Process simulation: observation of device structure and doping profile Simulation of 2-D MOSFETs through device and process simulations Simulation of novel 3-D transistors such as III-V HEMT, LEDs, FinFETs, GAA devices, solar cells etc, through device simulation 						
Essential Reading	Simulations, and Applications", 978-9814745512.	 C K Maiti, "Introducing Technology Computer-Aided Design (TCAD): Fundamentals, Simulations, and Applications", Jenny Stanford Publishing; 1st Edition, 2017, ISBN: 978-9814745512. Wu, Yung-Chun, Jhan, Yi-Ruei, "3D TCAD Simulation for CMOS Nanoeletronic 						
Supplementary Reading	 C K Sarkar, "Technology Computer Aided Design: Simulation for VLSI MOSFET", CRC Press, 1st Edition, 2013, ISBN: 978-1466512658. JP. Colinge, "FinFETs and Other Multi-Gate Transistors", Springer, 2008, ISBN: 978-0-387-71751-7 TCAD Manual (Available Online) 							

Course Name	SoPC and VLSI Testing Practice	Course Code	EC501	EC5013				
Offered by	Electronics and Communication	Structure(LTP	0			1.5		
Department	Engineering	C)	0	0	3	1.5		
To be offered for	M. Tech	Course Type	Core	'	•			
Prerequisite	NIL	Approved In	Senate	-44				
Learning Objectives	Design and development complete has	rdware/software sys	stem on l	FPGA an	d VLSI t	esting		
Learning Outcomes	able to effectively use commercially integrated systems, can able to efficient	tudent can able to design and develop the hardware/software system on FPGA, can ble to effectively use commercially available building block (IP) to construct highly ntegrated systems, can able to efficiently break down complex computational tasks into ardware and software components and build co-processor.						
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	 Verify fault coverage of test observe output Hands-on on Design for test testability Writing ATPG and Designs for Implement BIST for Memory Scan Chain based Sequential Fault Models simulations a Models Implement path delay fault t Introduction to System-Ontiming and Recoding Protocol and Interface, System Electronic system level modes based Design, Network on ch Soc Engineering and associ Level Design Capture and Systems 	(DFT) – insert testor Combinational ablocks Circuit Testing and verifications, esting Chip, Register Tr m-C Components, I delling, Transaction ip and Bus Structurated Tools, Architemthesis.	structur ansfer I Basic Soc onal leve res	scan cha ential Cir eal Testi Language Compor el model	reuits. Ing with e, Foldin ents, lling, As	Fault ng, Resertion n, High		
Essential Reading	 Wang, "VLSI Test Prir Elsevier; First edition (1 2. Louise H. Crockett, Stewart, The Zynq Book the Xilinx Zynq-7000 A ISBN: 099297870X. 	January 2011). IS Ross A. Elliot, M : Embedded Proces Il, 1 st edition, Stra	BN: 9380 artin A. sing with athclyde	0501552 Enderv n the AR Academ	vitz, Rob M Cortex ic Media	pert W. x-A9 on , 2014.		
Supplementary Reading	 Wayne Wolf, FPGA based System Design, 1st edition, Prentice Hall, 2004. ISBN: 0131424610. Steve Furber, ARM System on Chip Architecture, 2nd edition, Addison-Wesley, 2000. ISBN: 0201675196. 							

Course Name	Digital IC Design	Course Code	EC5014	1		
Offered by Department	Electronics and Communication Engineering	Structure(LTP	3	1	0	
To be offered for	M Tech	Course Type	Core			1
Prerequisite	NIL	Approved In	Senate-	.44		
Learning Objectives	 To impart in depth knowled design procedures for compl subsystems. Students would be able to do using semicustom and full c 	ge in CMOS digital ex combinational a esign and analyse c	nd sequer omplex d	ntial circ	uits and	[
Learning Outcomes	 To design series of masks reusing tool for higher level To model MOSFETs and Int To determine Noise margins ICs To develop combinational an and Pass Transistors To build arithmetic and Men 	erconnects in ICs , switching voltage d sequential circuit	delay pa	rameter	s, power	etc
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	 Issues in Digital Integrated Fabrication of CMOS IC and MOS Device: Threshold Volt Interconnect: Parameters, E CMOS Inverter: Transfer Ch Propagation Delay, Power (5 Combinational Logic Circuit Dynamic Logic, Cascading (7 Sequential Logic Circuits: Transfer Ch Arithmetic Building Blocks: Memory and Array Structur Flash Memory (5L+2T) Tutorials will include pen-palayout level 	packaging (4L+1T age, Secondary Effi- lectrical Wire Mode aracteristics, Noise (L+2T) s: Static CMOS, Pa (L+2T) aming Metrics, Stat (2T) Data paths in Digit es: ROM, RAM, CA	ects, SPICels, SPICE e margin, es-Transicand Dy tal Proces M, Peripl	E Wire M Capacit stors, D mamic L ssor Arch heral Cir ulation a	Models (2 cances, ynamic (catches, l nitecture reuitry, l at schem	CMC Regi es (7) PLA
Essential Reading	1. Jan M. Rabaey, Anantha Ch Circuits, 2 ND edition, Pears 0130909961	son, 2003. ISBN-10	: 0130909	963, ISI	3N-13: 9	78-
Supplementary Reading	 John E. Ayers, Digital Integrous Press, 2009. ISBN-10: 14200 R. Jacob Baker, CMOS Circu Blackwell, 2010. ISBN-10: 0 Sung-Mo (Steve) Kang, Yusu Circuits Analysis & Design, ISBN-10: 0073380628, ISBN 	6987X, ISBN-13: 9 uit Design, Layout, 470881321, ISBN-1 of Leblebici, Chilwo 4th edition, McGra	78-14200 and Simu 3: 978-04 o Kim, Cl w-Hill Hi	69877. ılation, 3 7088132 MOS Dig	3rd editi 23. gital Inte	on, V egra

Course Name	VLSI System Design	Course Code	EC5018	EC5015				
Offered by Department	Electronics and Communication Engineering	Structure(LTP C)	3	1	0	4		
To be offered for	M.Tech	Course Type	Core					
Prerequisite	NIL	Approved In	Senate-	-44				
Learning Objectives	To impart in depth knowledge in the circuits including both digital and ana	-		analyses	s of comp	olex VLSI		
Learning Outcomes	 integrated circuits Design and analyze complexity verification tools Gain proficiency in hardware 	 Understand circuits and system level issues while integrating sub blocks in integrated circuits Design and analyze complex VLSI systems using industry level design and verification tools Gain proficiency in hardware design and scripting languages 						
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	implementation options of VIS Modeling Styles (L5+1T) Designing Fast CMOS Circui EffortandOptimization, Low I Techniques at Circuit and Sy mitigation Techniques. (L8+T VLSI system design with HD dataflow, structural and mixe verificationofdesigns. Data pa circuits, arithmetic circuits an with HDL and design verifica Interconnect Design: Design i Parasitic, InterconnectTechni Distribution Networks, Clock Designs: Design consideration reliability. (L7+T2) Input/output Modules and ES Drivers, and ESD Protection (L5+T2)	 Gain proficiency in hardware design and scripting languages Review of VLSI, Classifications of VLSI Circuits, Design Methodologies and implementation options of VLSI Systems. Y-Chart, Design Abstraction Levels. Modeling Styles (L5+1T) Designing Fast CMOS Circuits, Various Techniques for Delay Estimation, Logical EffortandOptimization, Low PowerDesignTechniques, Power Management Techniques at Circuit and System Levels, Tradeoffs in Power & Delay and mitigation Techniques. (L8+T3) VLSI system design with HDL: Module concepts and modeling styles: Behavioral, dataflow, structural and mixed style modeling, Synthesis and verificationofdesigns. Data path subsystem design: Combinational and sequential circuits, arithmetic circuits and interconnects; implementation of such systems with HDL and design verification including postlayoutsimulations. (L7+T2) Interconnect Design: Design issues with Resistive, Capacitive and Inductive Parasitic, InterconnectTechniques, Power Distribution and Clock Design: Power Distribution Networks, Clock Generation and DistributionNetworks, Layout Designs: Design considerations for signal integrity, manufacturability and reliability. (L7+T2) 						
Essential Reading	Ming-Bo Lin, Introduction to VLSI Stress, 2012, ISBN:978-1-4398-6859.			-	_			
	1. Neil H. E. Weste, David Money Perspective, 4 th edition, Addison-	Wesley, Pearson, 2	013, ISB	N:978-0-	321-5477	4-3.		
Supplementary Reading	2. Liming Xiu, VLSI Circuit Design, Methodology Demystified, A conceptual Taxonomy, IEEE Press, A John Wiley & Sons, Inc., 2008, ISBN:978-0-470-12742-1.							
	3. Hubert Kaeslin, Morgan Kaufr ISBN: 978-0-12-800730-3.	nan, Top-Down D	igital VI	LSI Desi	ign, Elsev	vier,2015,		

Course Name	VLSI Technology	Course Code	EC5010	3				
Offered by Department To be offered for	Electronics and Communication Engineering M.Tech	Structure(LTP C) Course Type	3 Core	1	0	4		
Prerequisite	NIL	Approved In	Senate	-44				
Learning Objectives	To offer a profound understa							
Learning Outcomes	 Appreciate the intricacies inv Understand the various proce Learn fabrication steps for ex 	 Understand the various processes needed to fabricate the VLSI devices. Learn fabrication steps for existing and coming generation devices. 						
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	Fabrication. (L4+T1) Crystal Structure of Si, Defection Epitaxy, Vapour phase Epitaxy (L4+T1) Oxidation – Kinetics, Rate (L5+T2) Diffusion-Theory of Diffusting Implantation - Process, Ann (L5+T2) Lithography, immersion lithogeneous Etching-Wet Chemical Etching other materials (L3+T1) Deposition-Plasma Deposition contacts, Copper interconnecting IC BJT - LOCOS, Trends suitability for high-speed app	 Learn fabrication steps for existing and coming generation devices. Introduction to VLSI Design, Bipolar Junction Transistor Fabrication, MOSFET Fabrication. (L4+T1) Crystal Structure of Si, Defects in Crystal, Crystal growth (L3+T1) Epitaxy, Vapour phase Epitaxy, Doping during Epitaxy, Molecular beam Epitaxy (L4+T1) Oxidation – Kinetics, Rate constants, Dopant Redistribution, Oxide Charges (L5+T2) Diffusion-Theory of Diffusion, Doping Profiles, Diffusion Systems Ion Implantation - Process, Annealing of Damages, Masking during Implantation (L5+T2) Lithography, immersion lithography, e-beam lithography (L5+T2) Etching-Wet Chemical Etching, Dry Etching, Plasma Etching, Si, SiO₂, SiN and other materials (L3+T1) Deposition-Plasma Deposition, Metallization, Problems in Aluminium Metal contacts, Copper interconnects (L4+T1) IC BJT - LOCOS, Trench isolation, Poly-emitter-poly-base-BJT and its suitability for high-speed applications (L3+T1) MOSFET - Metal gate vs. Self-aligned Poly-gate, Tailoring of Device 						
Essential Reading	S. K. Ghandhi, VLSI Fabrication Prin					.,		
Supplementary Reading	1. S. M. Sze, VLSI Technology, 2. J. Plummer, M. D. Deal, P. I Practice and Modeling, Pears	B. Griffin, Silicon V	LSI Tecl	nnology,	Fundam	entals,		

Course Name	IC Design Practice	Course Code	EC501	EC5017					
Offered by	Electronics and Communication	Structure(LTP	0	0	4	2			
Department	Engineering	(C)	0	0	4	2			
To be offered for	M Tech	Course Type	Core			•			
Prerequisite	NIL	Approved In	Senate	-44					
Learning Objectives	based analog integrated ci conductor amplifiers and Digi • Students would be able to des	based analog integrated circuits especially operational amplifiers and trans conductor amplifiers and Digital integrated circuits.							
Learning Outcomes	 To be capable of simulating Schematic level analog circuits with at least 20+ transistors To be capable of generating layout with full custom / semicustom tools and to perform post layout simulations and extracting parameters to schematic model To design Digital building blocks using VHDL / Verilog To generate synthesizable design, create layout and post layout simulations for ASIC Design 								
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	 Design of analog ICs with Schematic and layout simulation using Cadence and Synopsys tools (6 weeks) Design of digital building blocks with Schematic and layout simulation using Cadence and Synopsys tools (6 weeks) Project will include identifying analog / digital IC from papers of IEEE JSSC, IEEETCASI, IEEE TCASII, IEEE TBioCAS, ISCAS, ISICAS, NEWCAS, APCCAS, MWCAS, simulate both schematic & layout and analyse the results. 								
Essential Reading	 Behzad Razavi, Design of An Hill Education, 2016, ISBN: Jan M. Rabaey, Anantha Ch Circuits, 2nd edition, Pearson 0130909961. 	nalog CMOS Integr. 978-0-07-252493-2 andrakasan, Borivo 1, 2003, ISBN-10: 0	ated Circ oje Nikoli 13090996	uits, 2nd ic, Digita 33, ISBN	l edition al Integra I-13: 978-	ated -			
Supplementary Reading	 Tony Chan Carusone, David Circuit Design, John Wiley & Paul R. Gray, Paul J. Hurst, Design Of Analog Integrated ISBN: 978-0- 470-24599-6 Sung-Mo (Steve) Kang, Yusu Circuits Analysis & Design, ISBN-10: 0073380628. Ronald Mehler, Digital Integ Verilog, 1st edition, Newnes, 	& Sons, Inc., 2012, I Stephen H. Lewis, I Circuits, 5th edition of Leblebici, Chilwo 4th edition, Mcgray grated Circuit Design	SBN: 978 Robert Con, John o Kim, Con, Hill High	8-0-470- G. Meyer Wiley & MOS Di gher Ed	77010-8. , Analysi Sons, In gital Inte ucation, 2	s And c., 2009. egrated 2014.			

Course Name	High level verification with System Verilog and UVM	Course Code	EC501	EC5018				
Offered By Department	Electronics and Communication Engineering	Structure(LTP C)	2	0	4	4		
To be offered for	M. Tech	Course Type	Core					
Prerequisite	Hold on Digital Logic Design, and HDL with design flow of VLSI Systems	Approved In	Senate					
Learning Objectives	To impart in depth knowledge and hands-on on the Design, Simulation and Verification Flow of Digital Circuits & Systems. Analyses of complex VLSI circuits including both digital and analog building blocks.							
Learning Outcomes	Students would be able to design a level Design and verification tools.			systems	using in	ldustry		
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	 Understand and use the features, including new data operators, relaxation of Ve enhancements to tasks and and interfaces, clocking block 100% coverage. Generate & analyse function coverage Basic UVM constructs & clast System Verilog/HDL verification stimulus, coverage, to utilize these features for meaning the Power and Clock Routing, Inc. 	 Overview of the HDL and Design Methodologies. Understand and use the System Verilog/HDL RTL design and synthesis features, including new data types, literals, procedural blocks, statements, and operators, relaxation of Verilog language rules, fixes for synthesis issues, enhancements to tasks and functions, new hierarchy and connectivity features, and interfaces, clocking blocks, assertions, cover. Verify the design to ensure 100% coverage. Generate & analyse functional coverage, code coverage, line coverage & FSM coverage Basic UVM constructs & classes, design a basic test environment using UVM System Verilog/HDL verification features, including classes, constrained random stimulus, coverage, strings, queues and dynamic arrays, and learn how to utilize these features for more effective and efficient verification. Power and Clock Routing, Interconnects design considerations 						
Essential Reading	Ming-Bo Lin, Introduction Perspective, CRC Press, 2012 SystemVerilog for Design: A Design and Modeling, 2 nd Edi	, ISBN:978-1-4398 A Guide to Using tion, ISBN-13: 978	-6859. System -0387333	Verilog 991	for Hard	lware		
Supplementary Reading	 Chris Spear, SystemVerilog fo Language Features, Springer Donald Thomas, Logic Desig ISBN: 1523364025. UVM Primer: A Step-by-St Methodology, 2013, ISBN: 09 	2012, ISBBN: 978 on and Verification open Introduction	3-1461407 n Using	7140. System	Verilog,	2016,		